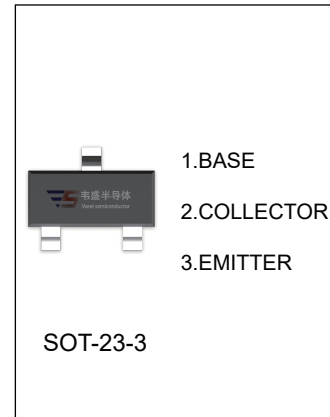


**M8550** TRANSISTOR(PNP)

**FEATURES**

Power dissipation


**MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector-Base Voltage	-40	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-25	V
V <sub>EBO</sub>	Emitter-Base Voltage	-6	V
I <sub>C</sub>	Collector Current	-800	mA
P <sub>C</sub>	Collector Power Dissipation	200	mW
R <sub>θJA</sub>	Thermal Resistance From Junction To Ambient	625	°C/W
T <sub>J</sub> , T <sub>stg</sub>	Operation Junction and Storage Temperature Range	-55~+150	°C

**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = -100μA, I <sub>E</sub> =0	-40		V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub> *	I <sub>C</sub> = -1mA, I <sub>B</sub> =0	-25		V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = -100μA, I <sub>C</sub> =0	-6		V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = -35V, I <sub>E</sub> =0		-0.1	μA
Collector cut-off current	I <sub>CEO</sub>	V <sub>CE</sub> = -20V, I <sub>B</sub> =0		-0.1	μA
DC current gain	h <sub>FE(1)</sub>	V <sub>CE</sub> =-1V, I <sub>C</sub> =-5mA	45		
	h <sub>FE(2)</sub>	V <sub>CE</sub> =-1V, I <sub>C</sub> =-100mA	85	400	
	h <sub>FE(3)</sub>	V <sub>CE</sub> =-1V, I <sub>C</sub> =-800mA	40		
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = -800mA, I <sub>B</sub> =-80mA		-0.5	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =-800mA, I <sub>B</sub> =-80mA		-1.2	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =-6V, I <sub>C</sub> = -20mA f=30MHz	150		MHz

\* PulseTest:pulse width ≤ 300μs, duty cycle ≤2%.

**CLASSIFICATION OF h<sub>FE(2)</sub>**

Rank	L	H
Range	85-300	300-400

